

MSE 104, Spring 2022 Quiz No. 2

Show all work and include units to receive full credit.

Check that all parts are answered.

Question	Points
1 (24 pts)	
2 (38 pts)	
3 (22 pts)	
4 (16 pts)	
Total	

1. Electrical Conductivity of Metals

- (a) Does sterling silver (an alloy of silver) have higher, same, or lower conductivity than that of pure silver? Justify your answer (6 pts).
- (b) State for copper whether electrical conductivity will increase or decrease with increasing temperature. Justify your answer. (6 pts)
- (c) Describe in your own words what an intrinsic semiconductor is? (3 pts)
- (d) Describe in your own words what an extrinsic semiconductor is? (3 pts)
- (e) When ceramic superconductor was immersed in liquid nitrogen and cooled below its critical temperature, it was able to levitate which of the following (6 pts)?
- A. itself above liquid surface
 - B. a magnet
 - C. itself above glass surface
 - D. a sugar cube

2. Semiconductors

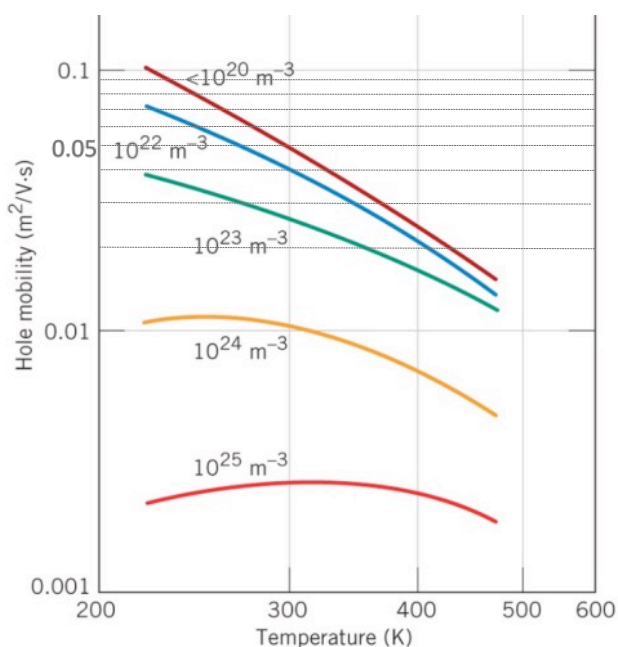
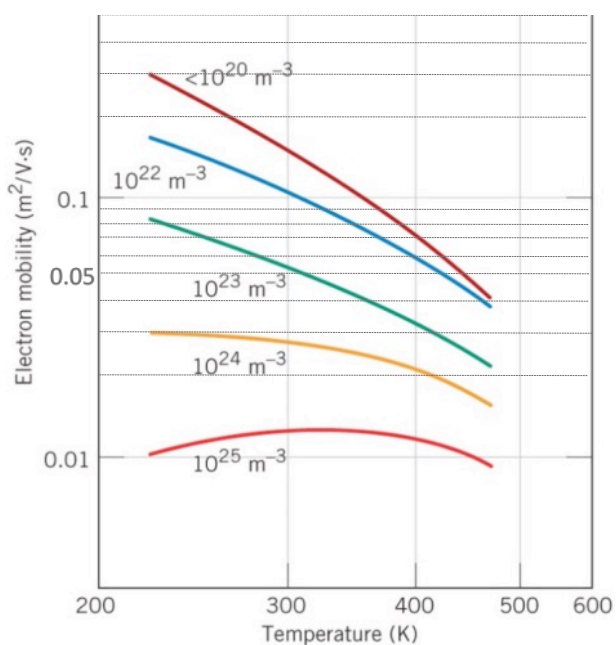
- (a) Draw a schematic plot and label all characteristic regions for the carrier concentration n versus temperature T for two materials (10 pts):
- A. an extrinsic n-type semiconductor
 - B. an intrinsic semiconductor.

(b) Name the majority charge carriers in cadmium (Cd) doped GaN semiconductor (4 pts)

(c) Name the majority charge carriers in gallium (Ga) doped CdS semiconductor (4 pts)

(d) A phosphorus (P)-doped silicon has at room temperature a conductivity of $0.25 \Omega^{-1} \text{ m}^{-1}$. What is the concentration of the majority charge carriers (in m^{-3})? The mobilities of electrons and holes in doped silicon as function of temperature are shown in graphs below (logarithmic scale). You will be given full credit as long as are within reasonable error limits and your process is correct (10 pts)

(e) Calculate the electrical conductivity of Si doped with $1 \times 10^{22} \text{ m}^{-3}$ of boron at 350K. (10 pts)



3. Electric Properties of Ceramics

(a) Briefly describe the three main origins of polarization in solid-state materials. (10 pts)

(b) A 1.0 kV voltage is applied on a dielectric film capacitor having an area of 100 cm^2 and a thickness of $10 \mu\text{m}$ (micrometers). The dielectric material has a dielectric constant of 3.0. Compute the capacitance and the stored energy density (J/cm^3). (12 pts)

4. Optical Properties

- (a) Give a 1-2 sentence explanation why adding lead (Pb) oxide in glass increases its index of refraction (4 pts)
- (b) ZnO has a bandgap of 3.4 eV. Is a ZnO crystal transparent, opaque, or colored? Provide a 1-2 sentence explanation (6 pts)
- (c) A laser beam is (choose one answer) (6 pts)
- A. coherent
 - B. of high intensity
 - C. highly collimated
 - D. all of the above

Useful equations, units, tables and constants:

$N_A = 6.02 \times 10^{23}/\text{mole}$

Units: $(\Omega\text{-m})^{-1} = \text{C}/(\text{m}\cdot\text{V}\cdot\text{sec})$

$k = 8.62 \times 10^{-5} \text{ eV/atom}\cdot\text{K}$

$e = 1.602 \times 10^{-19} \text{ C}$

$\epsilon_0 = 8.85 \times 10^{-12} \text{ F/m}$ [C/(V-m) or F is C/V]

$C = Q/V$

$E = V/l$

$p=qd$

$P = \Sigma qd/V_c$

$C = \epsilon_0 A/l$ (vacuum)

$C = \epsilon A/l$ (dielectric material)

$D_0 = \epsilon_0 E$ (vacuum)

$D = \epsilon E = \epsilon_0 E + P$ (dielectric material)

$\epsilon_r = \epsilon/\epsilon_0$

Stored dielectric energy equals to $\frac{1}{2}CV^2$

$\rho = RA/l,$

$\sigma = 1/\rho,$ where σ is electrical conductivity and ρ is electrical resistivity

$\sigma_{\text{total}} = n|e|\mu_e + p|e|\mu_h$ (if there are any holes)

$\sigma \approx \sigma_0 \exp(-E_g/2kT)$

$\sigma \approx \sigma_0 \exp(-\Delta E/kT)$

Key:
 [White Box] Metal
 [Grey Box] Nonmetal
 [Diagonal Box] Intermediate
 29 ← Atomic number
 Cu ← Symbol
 63.54 ← Atomic weight

IA																	0				
1 H 1.0080																	2 He 4.0026				
3 Li 6.939	4 Be 9.0122															5 B 10.811	6 C 12.011	7 N 14.007	8 O 15.999	9 F 18.998	10 Ne 20.183
11 Na 22.990	12 Mg 24.312	III B	IV B	VB	VIB	VII B	VIII						IB	II B	13 Al 26.982	14 Si 28.086	15 P 30.974	16 S 32.064	17 Cl 35.453	18 Ar 39.948	
19 K 39.102	20 Ca 40.08	21 Sc 44.956	22 Ti 47.90	23 V 50.942	24 Cr 51.996	25 Mn 54.938	26 Fe 55.847	27 Co 58.933	28 Ni 58.71	29 Cu 63.54	30 Zn 65.37	31 Ga 69.72	32 Ge 72.59	33 As 74.922	34 Se 78.96	35 Br 79.91	36 Kr 83.80				
37 Rb 85.47	38 Sr 87.62	39 Y 88.91	40 Zr 91.22	41 Nb 92.91	42 Mo 95.94	43 Tc (99)	44 Ru 101.07	45 Rh 102.91	46 Pd 106.4	47 Ag 107.87	48 Cd 112.40	49 In 114.82	50 Sn 118.69	51 Sb 121.75	52 Te 127.60	53 I 126.90	54 Xe 131.30				
55 Cs 132.91	56 Ba 137.34	Rare earth series	72 Hf 178.49	73 Ta 180.95	74 W 183.85	75 Re 186.2	76 Os 190.2	77 Ir 192.2	78 Pt 195.09	79 Au 196.97	80 Hg 200.59	81 Tl 204.37	82 Pb 207.19	83 Bi 208.98	84 Po (210)	85 At (210)	86 Rn (222)				
87 Fr (223)	88 Ra (226)	Actinide series																			

Factor by Which Multiplied	Prefix
10^9	giga
10^6	mega
10^3	kilo
10^{-2}	centi ^a
10^{-3}	milli
10^{-6}	micro
10^{-9}	nano
10^{-12}	pico

Table 18.6 Primary and Derived Units for Various Electrical Parameters and Field Vectors

Quantity	Symbol	SI Units	
		Derived	Primary
Electric potential	V	volt	$\text{kg}\cdot\text{m}^2/\text{s}^2\cdot\text{C}$
Electric current	I	ampere	C/s
Electric field strength	E	volt/meter	$\text{kg}\cdot\text{m}/\text{s}^2\cdot\text{C}$
Resistance	R	ohm	$\text{kg}\cdot\text{m}^2/\text{s}^2\cdot\text{C}^2$
Resistivity	ρ	ohm-meter	$\text{kg}\cdot\text{m}^3/\text{s}^2\cdot\text{C}^2$
Conductivity	σ	$(\text{ohm}\cdot\text{meter})^{-1}$	$\text{s}^2\cdot\text{C}^2/\text{kg}\cdot\text{m}^3$
Electric charge	Q	coulomb	C
Capacitance	C	farad	$\text{s}^2\cdot\text{C}^2/\text{kg}\cdot\text{m}^2$
Permittivity	ϵ	farad/meter	$\text{s}^2\cdot\text{C}^2/\text{kg}\cdot\text{m}^3$
Dielectric constant	ϵ_r	ratio	ratio
Dielectric displacement	D	farad-volt/ m^2	C/m^2
Electric polarization	P	farad-volt/ m^2	C/m^2

